

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-10 (canceled).

Claim 11 (currently amended): A method for removing a deposited film ~~inside a~~ from a member located in a vacuum apparatus, said vacuum apparatus having a chamber which comprises said method comprising:

providing a hot element in the chamber, said hot element disposed away from the deposited film, the hot element having at least a surface which comprises platinum;
placing a said member, in said chamber;
exhausting said chamber;
heating the hot element to 400°C. or higher without generating a plasma;
supplying into the chamber a cleaning gas containing at least one of a fluorine atom and a chlorine atom;
contacting the cleaning gas with the heated hot element to decompose and/or activate the cleaning gas and generate an activated species therefrom;
allowing the activated species to convert the deposited film into a gaseous substance; and
removing the gaseous substance from the chamber.

Claim 12 (previously presented): The method according to claim 11, wherein said chamber comprises a CVD apparatus and the method further comprises:

heating the hot element;
supplying a material gas to the chamber;
contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and
forming the deposited film which comprises at least one element from said material gas on a substrate.

Claim 13 (previously presented): The method according to claim 11, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.

Claim 14 (previously presented): The method according to claim 12, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.

Claim 15 (previously presented): The method according to claim 11, wherein said cleaning gas is a gas containing at least one of fluorine (F₂), chlorine (Cl₂), nitrogen trifluoride (NF₃), carbon tetrafluoride (CF₄), hexafluoroethane (C₂F₆), octafluoropropane (C₃F₈), carbon tetrachloride (CCl₄), pentafluorochloroethane (C₂ClF₅), trifluorochlorine (ClF₃), trifluorochloromethane (CClF₃), and sulfur hexafluoride (SF₆), and mixtures thereof.

Claim 16 (previously presented): The method according to claim 12, wherein said cleaning gas is a gas containing at least one of fluorine (F₂), chlorine (Cl₂), nitrogen trifluoride (NF₃), carbon tetrafluoride (CF₄), hexafluoroethane (C₂F₆), octafluoropropane (C₃F₈), carbon tetrachloride (CCl₄), pentafluorochloroethane (C₂ClF₅), trifluorochlorine (ClF₃), trifluorochloromethane (CClF₃), sulfur hexafluoride (SF₆), and mixtures thereof.

Claims 17-26 (canceled).

Claim 27 (currently amended): A method for removing a deposited film from a wall inside a chamber, said method comprising:

providing a hot element, said hot element disposed away from said wall and said deposited film, said hot element having at least a surface which is composed of platinum;

heating said hot element to 400° C. or higher without generating a plasma;

supplying said chamber with a cleaning gas containing at least one of a fluorine atom and a chlorine atom, and first contacting said hot element with said gas to thereby activate said gas;

thereafter contacting the deposited film with said activated cleaning gas and converting said deposited film into a gaseous substance; and

removing said gaseous substance from said chamber.

Claim 28 (previously presented): The method according to claim 27, wherein said chamber comprises a CVD apparatus and the method further comprises:

- heating the hot element;
- supplying a material gas to the chamber;
- contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and
- forming the deposited film which comprises at least one element from said material gas on a substrate.

Claim 29 (previously presented): The method according to claim 27, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.

Claim 30 (previously presented): The method according to claim 28, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.

Claim 31 (previously presented): The method according to claim 27, wherein said cleaning gas is a gas containing at least one of fluorine (F_2), chlorine (Cl_2), nitrogen trifluoride (NF_3), carbon tetrafluoride (CF_4), hexafluoroethane (C_2F_6), octafluoropropane (C_3F_8), carbon tetrachloride (CCl_4), pentafluorochloroethane (C_2ClF_5), trifluorochlorine (ClF_3), trifluorochloromethane ($CClF_3$), and sulfur hexafluoride (SF_6), and mixtures thereof.

Claim 32 (previously presented): The method according to claim 28, wherein said cleaning gas is a gas containing at least one of fluorine (F_2), chlorine (Cl_2), nitrogen trifluoride (NF_3), carbon tetrafluoride (CF_4), hexafluoroethane (C_2F_6), octafluoropropane (C_3F_8), carbon tetrachloride (CCl_4), pentafluorochloroethane (C_2ClF_5), trifluorochlorine (ClF_3), trifluorochloromethane ($CClF_3$), sulfur hexafluoride (SF_6), and mixtures thereof.

Claim 33 (new): The method according to claim 11, wherein said member is at least one of a measurement instrument, a sensor, a valve, and a pipe.